50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

1 September 2023

Product data sheet

1. General description

NPN/NPN Resistor-Equipped double Transistor (RET) in a medium power SOT1118D (DFN2020D-6) leadless Surface-Mounted Device (SMD) plastic package with side-wettable flanks (SWF).

NPN/PNP complement: PIMC32PAS-Q PNP/PNP complement: PIMP32PAS-Q

2. Features and benefits

- · 500 mA output current capability
- Built-in resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · Digital applications
- Cost-saving alternative to BC817 series in digital applications
- · Control of IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	500	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	4.1	4.55	5	

[1] See section "Test information" for resistor calculation and test conditions.



50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	6 5 4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2	7 8	TR1
5	12	input (base) TR2		R2 R1
6	01	output (collector) TR1	1 2 3	
7	01	output (collector) TR1	Transparent top view	
8	O2	output (collector) TR2	DFN2020D-6 (SOT1118D)	GND1 I1 O2 aaa-019894

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PIMN32PAS-Q	DFN2020D-6	plastic, leadless thermally enhanced ultra thin and small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1118D

7. Marking

Table 4. Marking codes

Type number	Marking code
PIMN32PAS-Q	8K

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

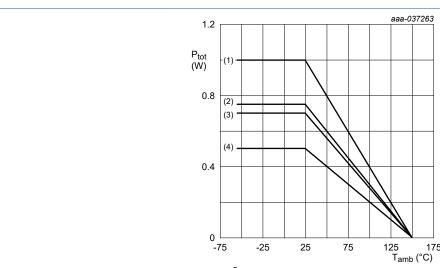
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or					
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
VI	input voltage			-5	12	V
Io	output current			-	500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	360	mW
			[2]	-	550	mW
			[3]	-	510	mW
			[4]	-	730	mW
Per device	<u> </u>			<u> </u>	'	'
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			[2]	-	750	mW
			[3]	-	700	mW
			[4]	-	1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35µm copper, tin-plated; mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint. [3]
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm²



(1) FR4 PCB, 4-layer copper, 1 cm²

PIMN32PAS-Q

- (2) FR4 PCB, single-sided, 35µm copper, 1 cm²
- (3) FR4 PCB, 4-layer copper, standard footprint
- (4) FR4 PCB, single-sided, 35µm copper, standard footprint

Per device: Power derating curves for DFN2020D-6 (SOT1118D) Fig. 1.

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50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	348	K/W
	junction to ambient		[2]	-	-	228	K/W
			[3]	-	-	246	K/W
			[4]	-	-	172	K/W
Per device	'			'			
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	167	K/W
			[3]	-	-	179	K/W
			[4]	-	-	125	K/W

- Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint.
- [2] [3] Device mounted on an FR4 PCB, single-sided, 35μm copper, tin-plated; mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm².

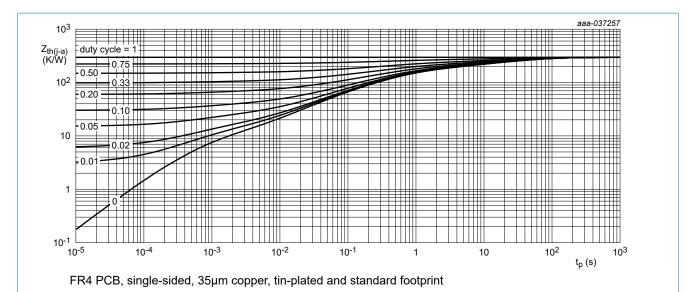
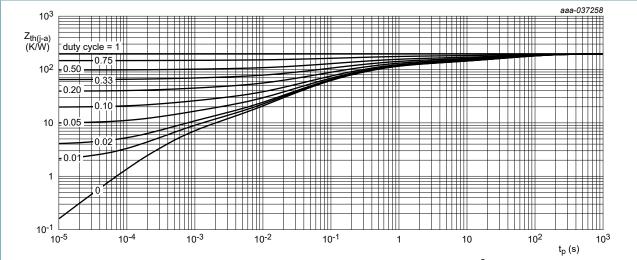


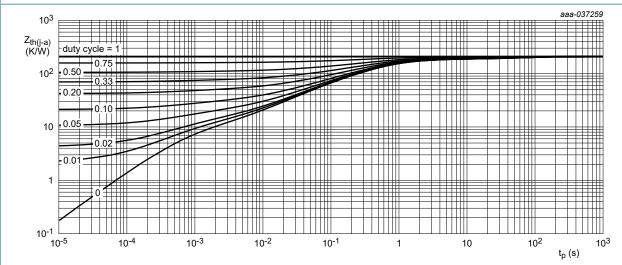
Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω



FR4 PCB, single-sided, 35µm copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

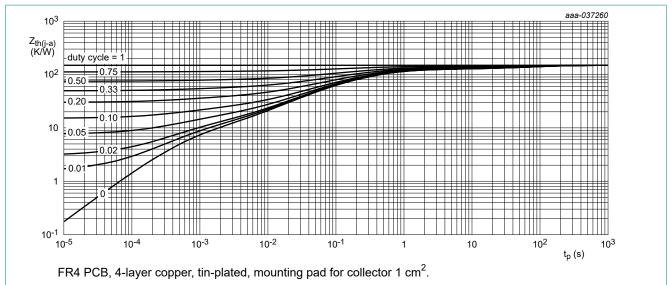


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

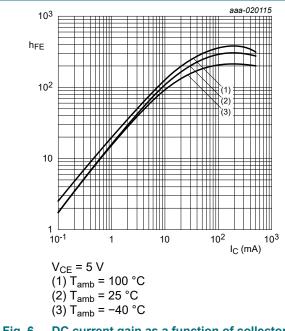
50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A; T _{amb} = 25 °C		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	= 10 mA; I _B = 0 A; T _{amb} = 25 °C		50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	r _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 50 V; I _B = 0 A; T _{amb} = 25 °C		-	-	0.5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	0.65	mA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 50 mA; T _{amb} = 25 °C		70	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	100	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		0.4	0.65	1	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		0.5	0.95	1.4	V
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	4.1	4.55	5	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$		-	5	-	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	210	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.



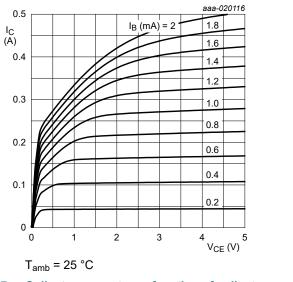
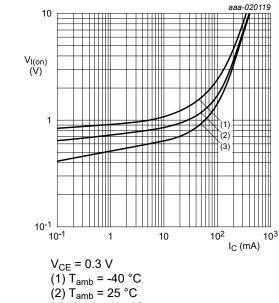


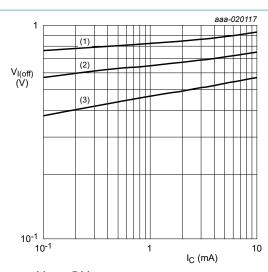
Fig. 7. Collector current as a function of collectoremitter voltage; typical values

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω



(3) T_{amb} = 100 °C

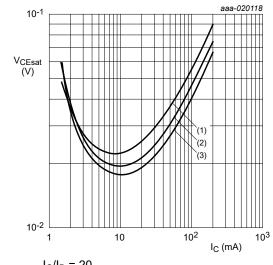
Fig. 8. current; typical values



 T_{amb} = 25 °C

V_{CE} = 5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

On-state input voltage as a function of collector | Fig. 9. Off-state input voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

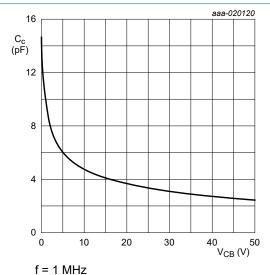
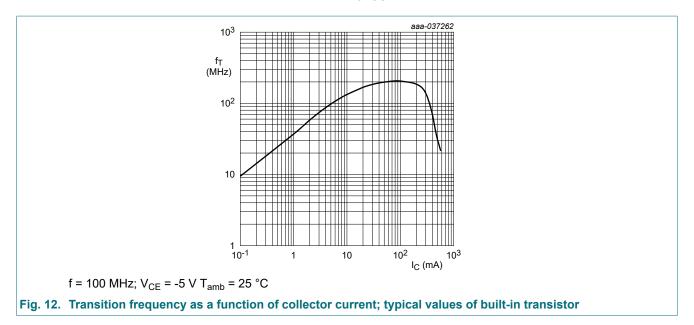


Fig. 11. Collector capacitance as a function of collectorbase voltage; typical values

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω



50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1):

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1):

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

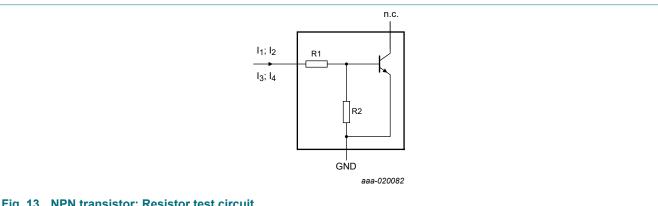


Fig. 13. NPN transistor: Resistor test circuit

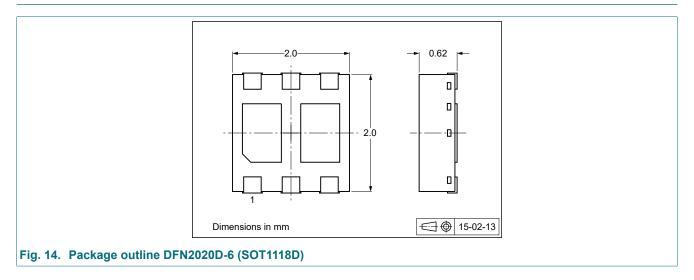
Resistor test conditions

Table 8. Resistor test conditions

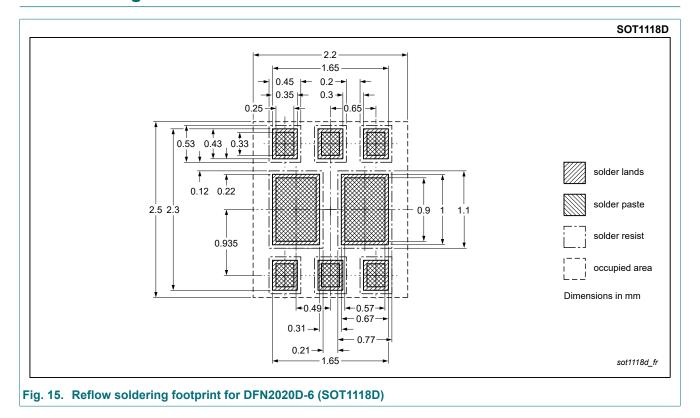
PIMN32PAS-Q	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	l ₂	l ₃	14
TR1/TR2 (NPN)	2.2	10	0.7 mA	0.8 mA	-0.45 mA	-0.55 mA

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

12. Package outline



13. Soldering



50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMN32PAS-Q v.1	20230901	Product data sheet	-	-

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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